

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

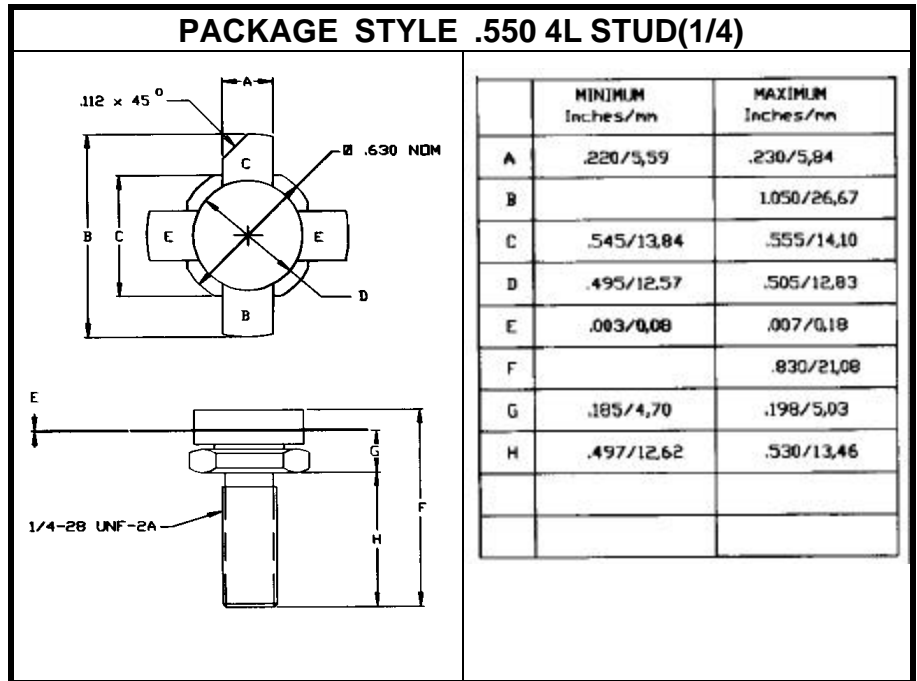
The **ASI TPV376** is a Common Emitter Device Designed for High Linearity Class A Television Band III (170-230 MHz) Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	16 A
V_{CB}	60 V
P_{DISS}	150 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
q_{JC}	1.2 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA	30			V
BV_{CER}	I _C = 100 mA R _{BE} = 10 Ω	60			V
BV_{CBO}	I _C = 100 mA	60			V
BV_{EBO}	I _E = 20 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		120	---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			150	pF
P_{out}	V _{CE} = 28 V I _C = 3.5 A f = 225 MHz	20			W
y	V _{CE} = 28 V I _E = 3.5 A P _{REF} = 20 W LOAD VSWR = ∞:1 f = 225 MHz	NO DEGRADATION IN OUTPUT POWER			
IMD₁	P _{ref} = 30 W VISION CARRIER = -8.0 dB SOUND CARRIER = -7.0 dB SIDEBAND SIG. = -16 dB V _{CE} = 28 V I _E = 3.5 A f = 225 MHz			-53	dB



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